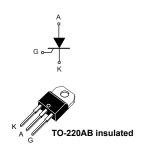


Standard 25 A 800 V SCR



Features

- On-state RMS current, I_{T(RMS)} 25 A
- Max. junction temperature = 125 °C
- Max. blocking voltage = V_{DRM}, V_{RRM} = 800 V
- I_{GT} maximum = 40 mA
- High immunity dV/dt = 1500 V/μs
- ECOPACK®2 compliant component (RoHS and HF compliance)
- Packaged in an insulated TO-220AB
 - Insulating voltage 2500 V_{RMS}
 - UL1557 certified (file ref. E81734)

Applications

- Solid State Relay (SSR)
- Bypass
- AC DC Inrush Current Limiter (ICL)
- Battery Charger
- AC DC voltage controlled rectifier
- · Off board automotive battery charger
- · Motor soft starter

Product status link			
TXN8	TXN825RG		
Product :	Product summary		
Symbol Value			
I _{T(RMS)}	25 A		
V _{DRM} /V _{RRM}	800 V		
I _{GT}	40 mA		
Tj	125 °C		

Description

Available in through-hole package, the TXN825RG is suitable for general purpose applications.

It uses clip assembly technology, therefore the performance is superior in surge current capabilities.

Housed in a TO-220AB ceramic insulated, this device provides an improved thermal resistance.



1 TXN825RG Characteristics

Table 1. Absolute ratings (limiting values), $T_j = 25$ °C unless otherwise specified

Symbol	Parameter			Value	Unit
I _{T(RMS)}	RMS on-state current (180° conduction angle)		T _C = 83 °C	25	
I _{T(AV)}	Average on-state current (180° conduction	n angle)	16 - 83 C	16	Α
L	I _{TSM} Non repetitive surge peak on-state current		t _p = 10 ms	300	
ITSM			t _p = 8.3 ms	314	Α
l²t	I²t value for fusing		t _p = 10 ms	450	A²s
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, tr $\leq 100 \text{ ns}$ f = 50 Hz			50	A/µs
V _{DRM} / V _{RRM}	Repetitive surge peak off-state voltage (50-60 Hz) $T_j = 125 ^{\circ}\text{C}$		800	V	
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 125 °C	4	Α
P _{G(AV)}	Average gate power dissipation	Average gate power dissipation $T_j = 125 ^{\circ}\text{C}$			W
T _{stg}	Storage junction temperature range			-40 to +150	°C
Tj	Operating junction temperature range			-40 to +125	°C
V _{RGM}	Maximum peak reverse gate voltage			5	V
V _{INS}	Insulation RMS voltage, 1 minute, UL1557 certified E81734			2.5	kV

Table 2. Electrical characteristics (T_j = 25 °C unless otherwise specified)

Symbol	Test conditions			Value	Unit
la-				4	mA
IGI	V_{D} = 12 V, R_{L} = 30 Ω		Max.	40	IIIA
V _{GT}			Max.	1.3	V
V_{GD}	$V_D = V_{DRM}$, $R_L = 3.3 \text{ k}\Omega$, $T_j = 125 ^{\circ}\text{C}$		Max.	0.2	V
I _H	I _T = 500 mA, gate open		Max.	50	mA
IL	$I_{G} = 1.2 \times I_{GT}$		Max.	90	mA
dV/dt	V_D = 536 V, gate open T_j = 125 °C		Min.	1500	V/µs

Table 3. Static characteristics

Symbol	Test conditions			Value	Unit
V _{TM}	I _{TM} = 50 A, t _p = 380 μs	T _j = 25 °C	Max.	1.60	V
V _{t0}	Threshold voltage	T _j = 125 °C	Max.	0.77	V
R _d	Dynamic resistance	T _j = 125 °C	Max.	14	mΩ
I _{DRM} / I _{RRM}	V _{DRM} = V _{RRM} = 800 V	T _j = 25 °C	Max.	5	μΑ
		T _j = 125 °C	Max.	4	mA

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6

0

0.5

0.0

Table 4. Thermal parameters

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Thermal resistance Junction to case (DC)	2.0	°C/W
R _{th(j-a)}	j-a) Junction to ambient (DC) 60		C/VV

1.1 Characteristics (curves)

average on-state current

P(W)

22

20

18

16

14

12

10

8

6

α

12

10

Figure 1. Maximum average power dissipation versus

Figure 2. Average and D.C. on-state current versus case temperature $I_{T(AV)}(A)$ 28 26 D.C 24 22 20 18 $\alpha = 180$ 16 14 12 10 8 6 2 $T_{\mathbb{C}}(^{\circ}\mathbb{C})$ 0 0 25 50 75 100 125

ambient temperature

3.0 | T(AV)(A) |
2.5 | D.C. |
2.0 | α = 180° |
1.5 | 1.0 |

 $T_a(^{\circ}C)$

75

50

Figure 3. Average and D.C. on-state current versus

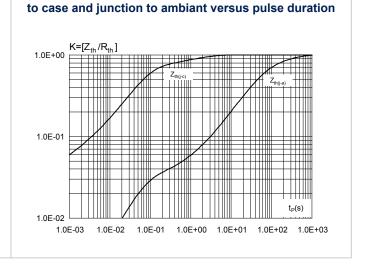


Figure 4. Relative variation of thermal impedance junction

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125



Figure 5. Relative variation of gate trigger and holding current versus junction temperature

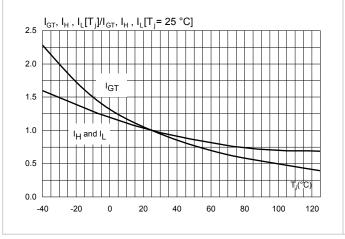


Figure 6. Surge peak on-state current versus number of cycles

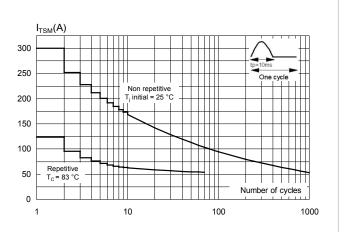


Figure 7. Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10 ms

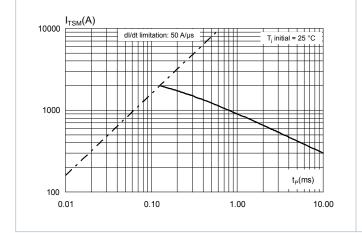
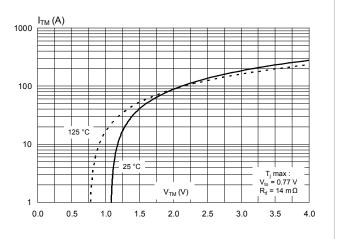


Figure 8. On-state characteristics (maximum values)



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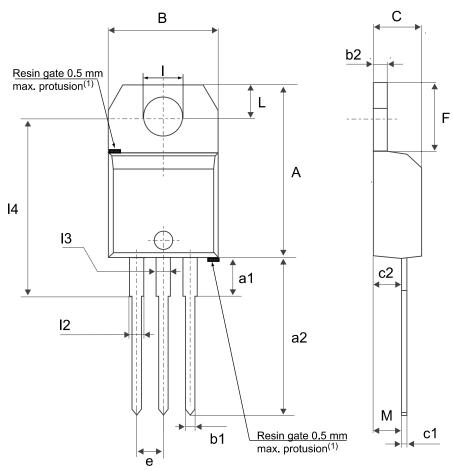
Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

2.1 TO-220AB insulated package information

- Epoxy resin is halogen free and meets UL94 flammability standard, level V0
- Lead-free plating package leads
- Recommended torque: 0.4 to 0.6 N·m

Figure 9. TO-220AB Insulated package outline



(1)Resin gate position accepted in one of the two positions or in the symmetrical opposites.

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Table 5. TO-220AB Insulated package mechanical data

			D	imensions			
Ref.		Millimeters		Inches ⁽¹⁾			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	15.20		15.90	0.5984		0.6260	
a1		3.75			0.1476		
a2	13.00		14.00	0.5118		0.5512	
В	10.00		10.40	0.3937		0.4094	
b1	0.61		0.88	0.0240		0.0346	
b2	1.23		1.32	0.0484		0.0520	
С	4.40		4.60	0.1732		0.1811	
c1	0.49		0.70	0.0193		0.0276	
c2	2.40		2.72	0.0945		0.1071	
е	2.40		2.70	0.0945		0.1063	
F	6.20		6.60	0.2441		0.2598	
ı	3.73		3.88	0.1469		0.1528	
L	2.65		2.95	0.1043		0.1161	
12	1.14		1.70	0.0449		0.0669	
13	1.14		1.70	0.0449		0.0669	
14	15.80	16.40	16.80	0.6220	0.6457	0.6614	
М		2.6			0.1024		

^{1.} Inch dimensions are for reference only.

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3 TXN825RG Ordering information

Figure 10. Ordering information scheme

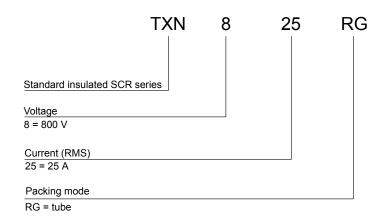


Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TXN825RG	TXN825	TO-220AB-Ins.	2.3 g	50	Tube

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Revision history

Table 7. Document revision history

Date	Revision	Changes
23-Feb-2018	1	Initial release.
01-Jun-2018	2	Removed maturity status indication from cover page. The document status is production data.

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